

版次	新版本	旧版本	修改单位	修改内容
2016-06-01	1.0	NA	研发部	新文件制成(因工程产品,故 RD 开头)
2020-06-29	1.1	1.0	研发部	增加 SOT89(导电胶)封装
2020-07-28	1.2	1.1	研发部	更新 SOT23-5 脚位
2020-08-03	1.3	1.2	研发部	增加应用信息,更新联系方式
2020-08-11	1.4	1.3	研发部	增加典型性能特性
2020-08-13	1.5	1.4	研发部	增加典型应用电路,更新S0T23-5脚位
2022-10-09	1.6	1.5	研发部	更新电压



General Description

SE85XX series is designed for power-sensitive applications. It includes a precision and high voltage input stage, an ultra-low-power bias current branch, and results in a ultra-low-power and low-dropout linear regulator.

The SE85XX operates from an input voltage of V_{OUT} +1V to 35V, consumes only 2.5 μ A of quiescent current, and offers 1% initial accuracy and low dropout voltage, 300mV typical at 100mA.

SE85XX has 1.8V, 2.8V, 3.0V, 3.3V, 3.6V, 5.0V fixed voltage versions.

Other features include short-circuit protection and thermal shutdown.

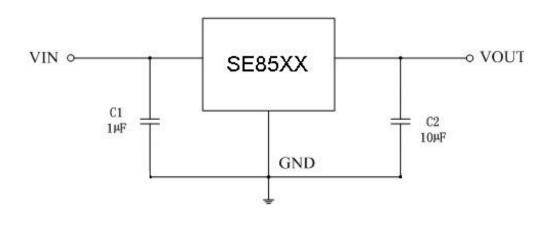
Features

- Ultra Low Quiescent Current: 2.5 µ A(Typ.)
- Wide Operating Voltage: V_{OUT}+1V to 35V
- High output current: ≥200mA
- System startup with no overshoot
- Short circuit protection is designed with no overshoot
- UVLO 1.8V
- Low Dropout Voltage
- High Accuracy Output Voltage: ±1%
- Excellent power / load transient response
- Low temperature coefficient: ±100ppm/°C
- Thermal and Short-Circuit Protection
- SOT-89、SOT-23、SOT23-5 package
- Customer Pin Assignments are available

Applications

- Battery-powered Smoke sensor
- Smoke sensor
- Microcontrollers
- Household appliances and instruments

Application Diagram

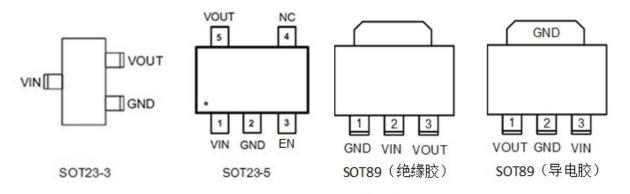


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Pin Configuration

(Customer pin assignments are available)

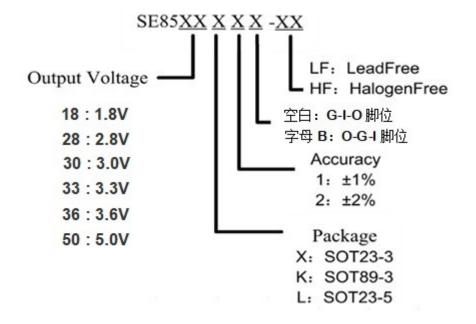


Absolute Maximum Rating

Symbol	Parameter	Value	Units	
V _{IN}	Input Supply Voltage	40	V	
V _{OUT}	Output Voltage	6		
T _A	Operating Temperature	-40105		
T _{STG}	Storage Temperature	-40150	°C	
TJ	Maximum Junction Temperature	150		
T _{LEAD}	Lead Temperature (Soldering) 10 seconds	260		
		165(SOT89)		
θ_{JA}	Thermal Resistance, Junction-to-Ambient	280(SOT23)	°C/W	
		750 (SOT89)		
P _D	Power Consumption	250 (SOT23)	mW	
Electrostatic	Human Body Model(HBM)	4	kV	
discharge rating	Charged Device Model (MM)	100	V	



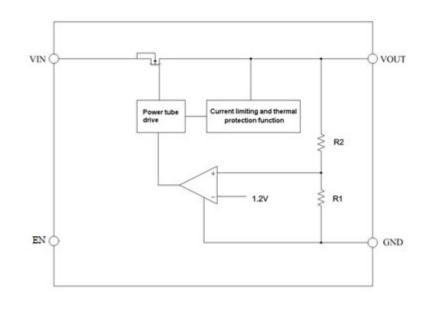
Ordering Information



Operating Rating

Parameter	Value	Units
Operating Temperature	-20°C~85	°C
Storage Temperature	-40℃~125	°C
Lead Temperature (Soldering) 10 seconds	260±5	°C

Block Diagram



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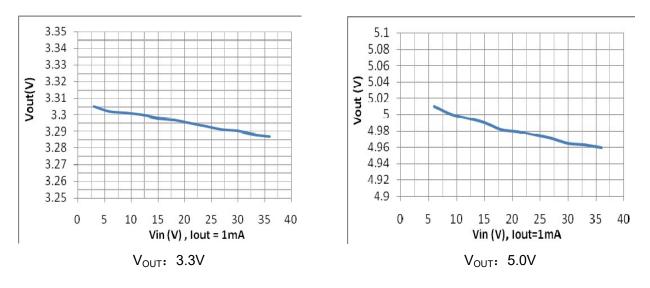


Electrical Characteristics

 $(V_{IN}=V_{OUT}+1V; Tj=25^{\circ}C \text{ unless otherwise noted.})$

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{IN}	Input Supply Voltage		1.8		36	V
V _{OUT}		I _{OUT} =10mA	-1%		1%	V
V OUT	Output Voltage Accuracy		-2%		2%	V
Ι _Q	Quiescent Current			2.5	6.0	μA
I _{OUT}	Output Current		200	250		mA
		I _{OUT} =10mA ΔV _{OUT} = - V _{OUT} *2%		30		mV
V _{DROP}	Dropout Voltage	I _{OUT} =100mA ΔV _{OUT} = - V _{OUT} *2%		300		mV
		I _{OUT} =200mA ΔV _{OUT} = - V _{OUT} *2%		600		mV
V _{LR}	Load Regulation	1mA ≤ I _{OUT} ≤ 100mA		40		mV
V _{SR}	Line Regulation	I _{OUT} =1mA, V _{IN} =(V _{OUT} +1V) to 30V		0.02		%/V
PSRR	Power Supply Rejection Ratio	Vin=12V , lout=10mA F=1Khz,Vout=3.3V		80		dB
V _{ENH}	Enable High Level	Enabled	1			V
V _{ENL}	Enable Low Level	Disabled		_	0.4	V
I _{EN}	EN Current	EN=0~V _{IN} (R _{EN} =100K)		1		μA
I _{LIMIT}	Current Limit	V _{IN} =(V _{OUT} +1V) to 30V R _{LOAD} =V _{OUT} /1A		450		mA
TSHDN	Thermal Protection			150		°C
TC _{VOUT}	Output Voltage Temperature Coefficient	I _{OUT} =10mA -40°C≤T _{AMB} ≤100°C		±100		ppm/°C

Typical Performance Characteristics



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40V/2µA/200mA, Ultra-Low-Iq, Low Dropout LDO

20 40 6 Temperature (C)

V_{OUT}: 5.0V

60

80

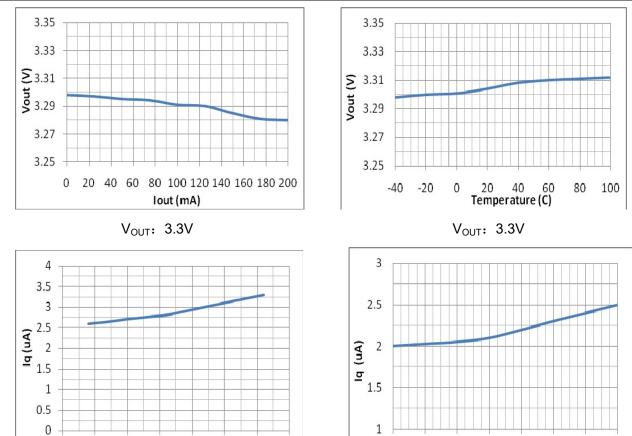
100

-40

-20

0

SE85XX



 V_{OUT} : 3.3V

20 25 30 Vin (V), No Load

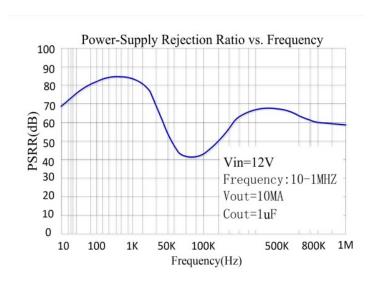
35

40

5

10

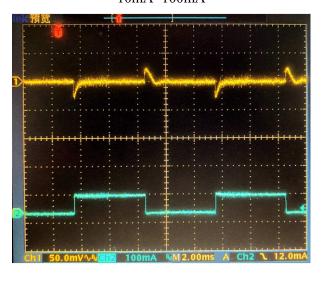
15



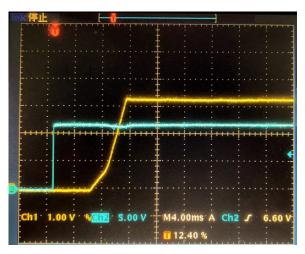
Load Transient (Vin=12V) 10mA~100mA

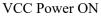
SEAWARD

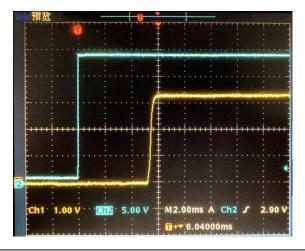
ELECTRONICS



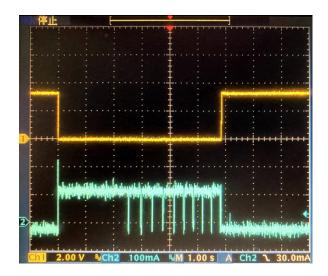
EN OFF**→**ON



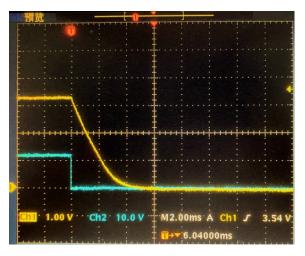








EN ON➔ OFF (No Load) Discharge





APPLICATION INFORMATION INPUT CAPACITOR

An input ceramic capacitor of 1μ F is required between the VIN and GND pin. The capacitor shall be placed as close as possible to VIN pin, and the wide copper trace is also recommended.

OUTPUT CAPACITOR

The recommended is 10 μ F ceramic capacitor. The minimum capacitance for stable and correct operation is 1 μ F. The higher the value of this output capacitor, the lower the ripple during the operations. The output capacitor should be placed as close to the Output Pin as possible. The wide copper trace is recommended.

NO-LOAD STABILITY

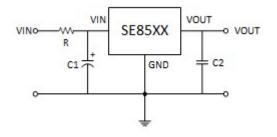
The SE85XX will remain stable and in regulation with no external load. This is especially important in CMOS RAM keep-alive applications.

FOLD-BACK SHORT-CIRCUIT PROTECTION

When short-circuit occurs, SE85XX will fold back the short-circuit currents to a pre-determined lower level, This will reduce excessive heat in otherwise large current conditions. This feature provides another level of protection to IC itself and also the whole system.

IN-RUSH CURRENT AND VOLTAGE

The following figure shows a typical application circuit for the SE85XX devices. Please keep in mind that in-rush current can push up the Vin overshoot by as much as 50%. For example, when Vin=30V, the in-rush caused spike voltage can be as high as 45V. Therefore the voltage rating of Cin needs to be higher than 50% of the application.



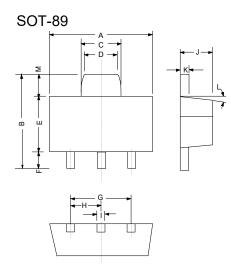
In live insertion application, it is suggested that R, C1 are selected as following:

 $1.C1=10\mu F \sim 100\mu F$ ceramic or electrolytic capacitor with maximum voltage greater than 50V, R=0

2.If the average current is known, for example a t 10mA, then for an input voltage of 20V, the C1 =1 μ F ~ 10 μ F ceramic or electrolytic with maxim um voltage greater than 40V and R=1K Ω in the type of 1206 at 1/4W rating can be selected.

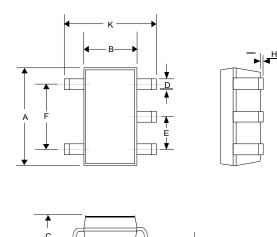


Outline Drawing for SOT-89



DIM ENSIO NS					
DIM ^N	INCHES		MM		
DIN	MIN	M AX	MIN	M AX	
А	0.173	0.181	4.400	4 .600	
В	0.159	0.167	4.050	4 .250	
С	0.067	0.075	1.700	1.900	
D	0.051	0.051 0.059		1.500	
E	0.094	0.102	2.400	2 .600	
F	0.035	0 .047	0.890	1.200	
G	0.118REF		3.00 REF		
Н	0.059REF		1.50 REF		
	0.016	0 .020	0.400	0 .520	
J	0.055	0.063	1.400	1.600	
K	0.014	0 .016	0.350	0 .410	
L	10 °TYP		10 °TYP		
М	0.028REF		0.70 REF		

Outline Drawing for SOT-23-5



DIMENSIONS					
DIM ^N	INCHES		MM		
DIIVI	MIN	MAX	MIN	MAX	
Α	0.110	0.120	2.80	3.05	
В	0.059	0.070	1.50	1.75	
С	0.036	0.051	0.90	1.30	
D	0.014	0.020	0.35	0.50	
Ш	-	0.037	-	0.95	
ш	-	0.075	-	1.90	
Н	-	0.006	-	0.15	
J	0.0035	0.008	0.090	0.20	
K	0.102	0.118	2.60	3.00	



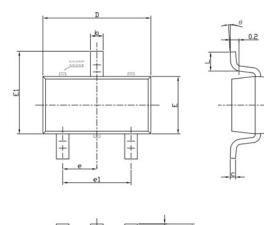
Max

Dimensions in Inches

Max

MIn

Outline Drawing for SOT-23-3

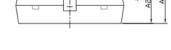


Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
с	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
е	0.950	(BSC)	0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Dimensions In Millimeters

MIn

Symbol



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